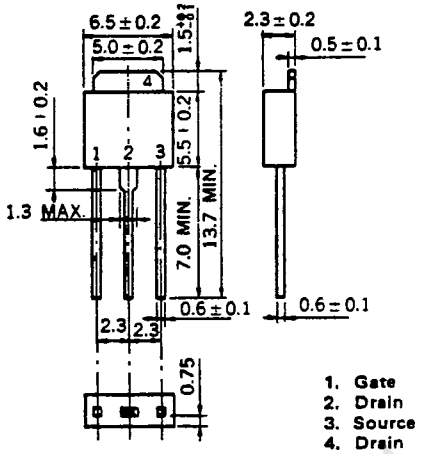
MOS FIELD EFFECT POWER TRANSISTOR
2SK612

FAST SWITCHING
N-CHANNEL SILICON POWER MOS FET
INDUSTRIAL USE

PACKAGE DIMENSIONS (Unit: mm)



FEATURES

- Suitable for switching power supplies, actuater controls, and pulse circuits.
- Low $R_{DS(on)}$
- No second breakdown
- 4 V Gate Drive – Logic level –

ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

Drain to Source Voltage	V_{DSS}	100	V
Gate to Source Voltage	V_{GSS}	±20	V
Continuous Drain Current	$I_{D(DC)}$	±2	A
Peak Drain Current	$I_{D(pulse)}$*	±8	A
Total Power Dissipation	P_T**	20	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	−55 to +150	°C

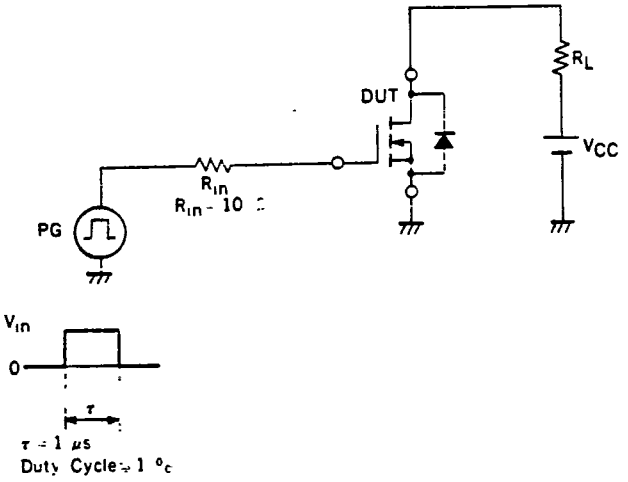
* PW ≦ 10 ms, Duty Cycle ≦ 50 %

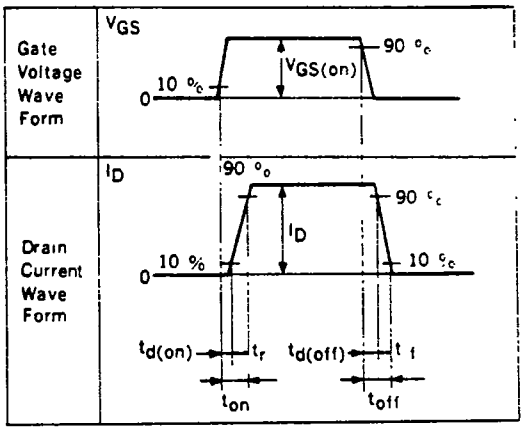
** T_C = 25 °C

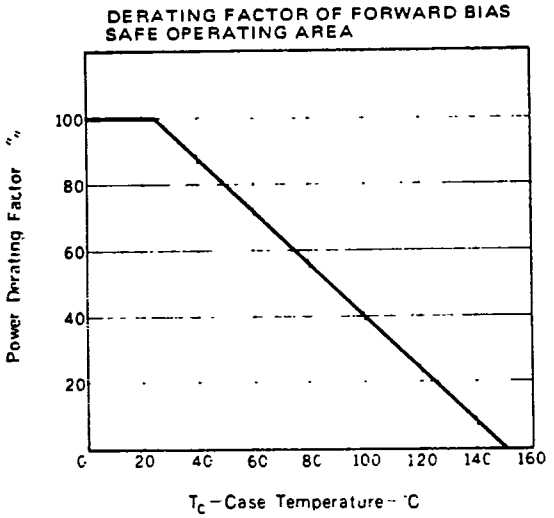
ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

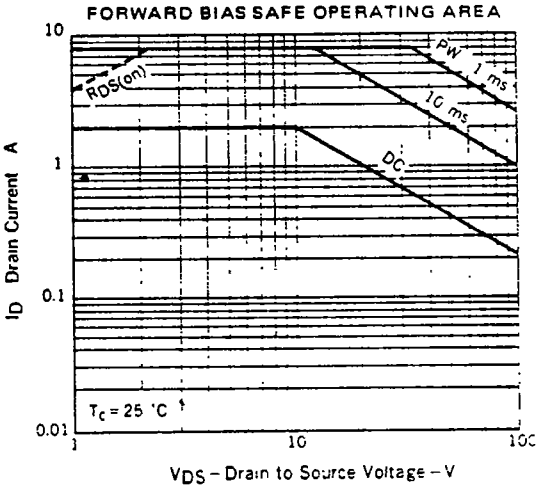
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain Leakage Current	I_{DSS}			10	μA	V_{DS} = 80 V, V_{GS} = 0
Gate to Source Leakage Current	I_{GSS}			±100	nA	V_{GS} = ±15 V, V_{DS} = 0
Gate to Source Cutoff Voltage	$V_{GS(off)}$	0.8		3.0	V	V_{DS} = 10 V, I_D = 1 mA
Forward Transfer Admittance	$\|y_{fs}\|$	1.0			S	V_{DS} = 10 V, I_D = 1 A
Drain to Source On-State Resistance	$R_{DS(on)}$		0.3	0.45	Ω	V_{GS} = 10 V, I_D = 1 A
Drain to Source On-State Resistance	$R_{DS(on)}$		0.35	0.6	Ω	V_{GS} = 4 V, I_D = 0.8 A
Input Capacitance	C_{iss}		500		pF	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz
Output Capacitance	C_{oss}		120		pF	
Reverse Transfer Capacitance	C_{rss}		30		pF	
Turn-On Delay Time	$t_{d(on)}$		10		ns	I_D = 1 A, V_{CC} = 50 V, $V_{GS(on)}$ = 10 V, R_L = 50 Ω, R_{in} = 10 Ω
Rise Time	t_r		20		ns	
Turn-Off Delay Time	$t_{d(off)}$		80		ns	
Fall Time	t_f		20		ns	

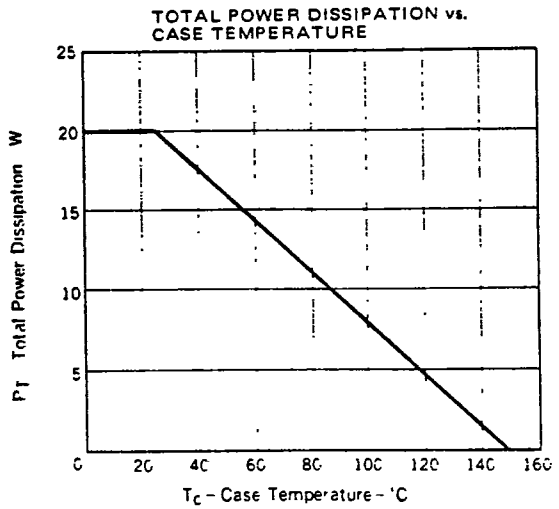
TURN-ON AND TURN-OFF TIME TEST CIRCUIT

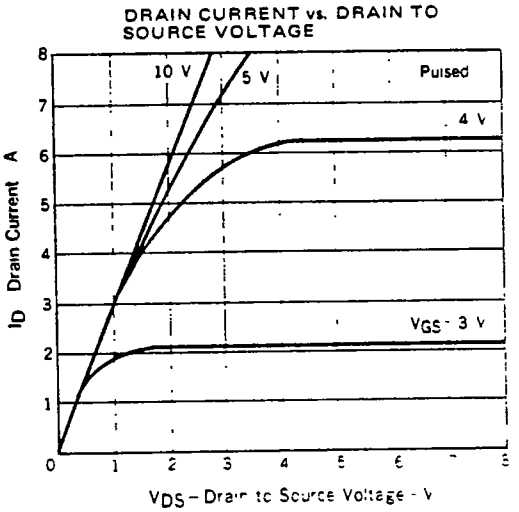




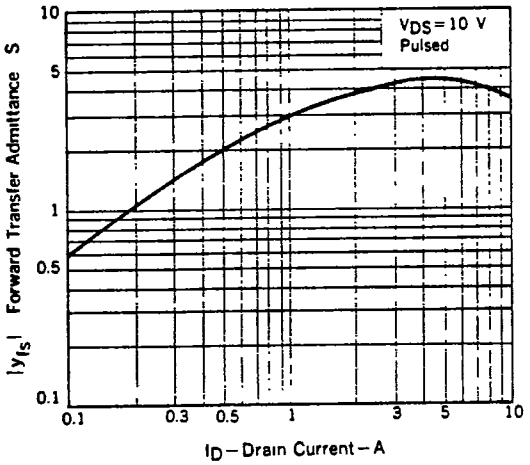




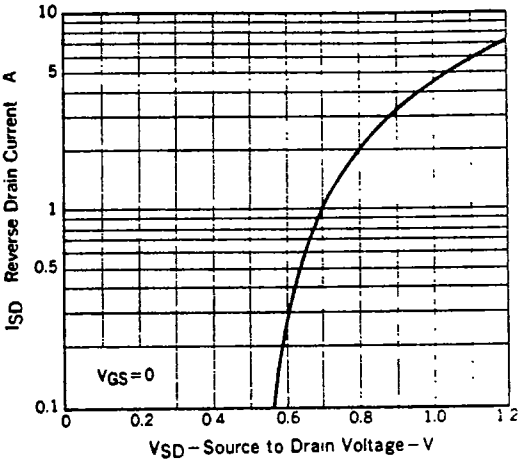




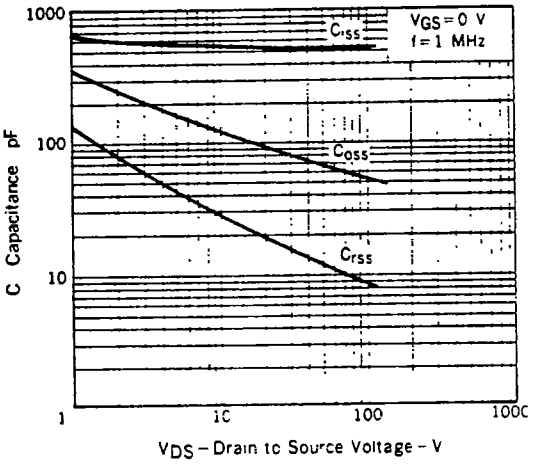
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



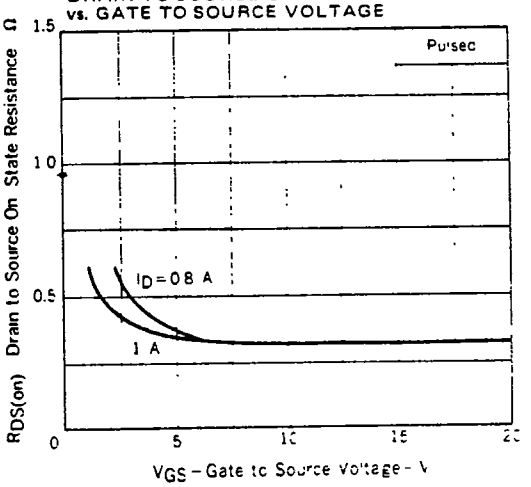
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



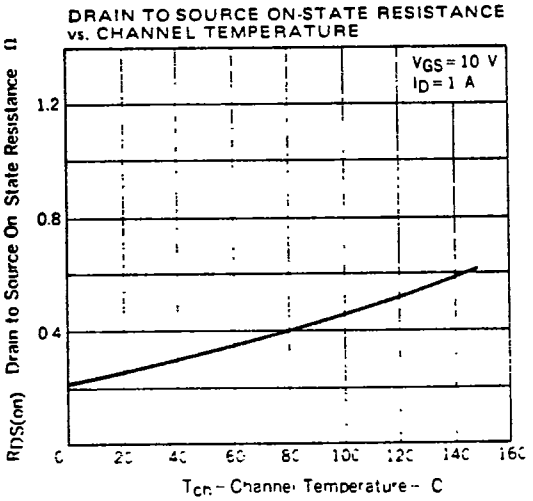
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



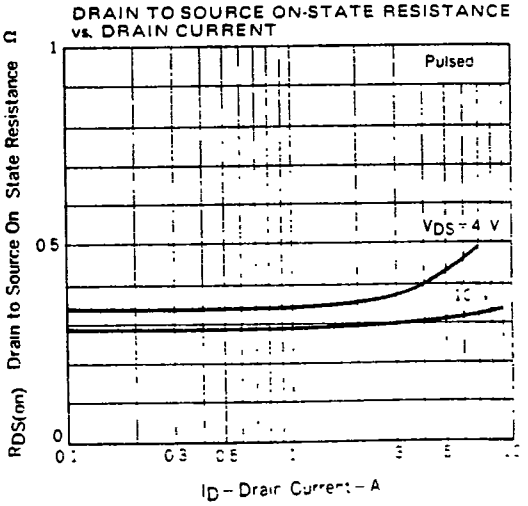
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



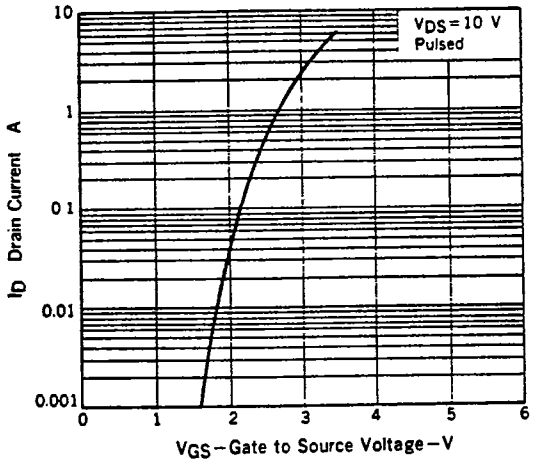
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



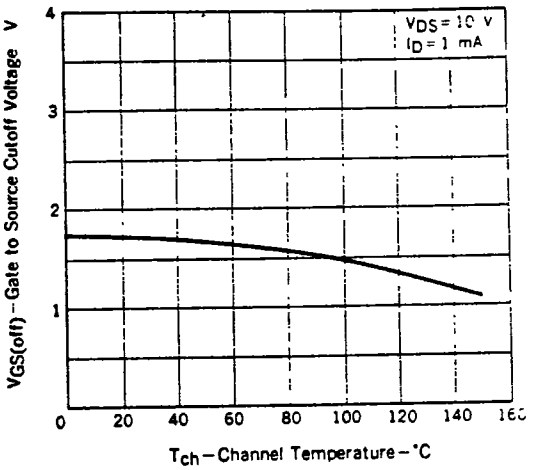
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



TRANSFER CHARACTERISTIC



GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



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